

BUV20, BUV21, BUV22, BUV23, BUV24

NPN Silicon Low Frequency High Power Switching Transistor



Features:

1. Heavy working current. Good temperature stability. Excellent thermal fatigue capability.
2. Good Switching Characteristic.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch, low frequency power amplify, power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications										
			BUV20		BUV21		BUV22		BUV23		BUV24		
Total Dissipation (Tc=25°C)	P _{tot}	W	250										
Max. Collector Current	I _{CM}	A	50		40		40		30		20		
Junction Temperature	T _{jm}	°C	175										
Collector-Base Breakdown Voltage	V _{(BR)CBO}	V	≥160		≥250		≥300		≥400		≥450		
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	V	≥125		≥200		≥250		≥325		≥400		
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	V	≥7										
			I _E =1mA										
Collector- Emitter Saturation Voltage Drop	I _C = I _B =	V	≤1.2	50A 5A	≤1.5	25A 3A	≤1.5	20A 2.5A	≤0.8	8A 1.6A	≤0.6	6A 1.2A	
Collector-Emitter Laekage Current	I _{CEO}	mA	≤3.0										
			V _{CE} =100V	V _{CE} =160V	V _{CE} =200V	V _{CE} =250V	V _{CE} =300V						
Emitter-Base Laekage Current	I _{EBO}	mA	≤1.0 (V _{EB} =7V)										
DC Current Gain V _{CE} =, I _C =	h _{FE}		20~60					15~60					
			2V, 25A	2V, 12A	4V, 10A	4V, 8A	4V, 6A						
Transition frequency	f _T	MHz	≥8 (V _{CE} = 15V, I _C =2A, f=4MHz)										
Rise Time	V _{CE} =	t _r	us	≤1.5	30V	≤1.2	100V	≤1.3	100V	≤0.8	100V	≤1.6	120V
Storage Time	I _C =	t _s	us	≤1.2	50A, 5A	≤1.8	25A 3A	≤2.5	20A 2.5A	≤2.5	16A 3.2A	≤2.3	12A 2.4A
	I _{B1} =												
Fall Time	I _{B2} =	t _f	us	≤0.3	-5A	≤0.4	-3A	≤0.5	-2.5A	≤1.0	-3.2A	≤1.4	-2.4A

Outline and Dimensions: